

GENERAL DESCRIPTION

The ASM5853 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and low gate charge. A schottky diode is provided to facilitate the implementation of a bidirectional blocking switch, or for DC-DC conversion applications.

APPLICATIONS

- ◆ DC-DC conversion application
- ◆ Load switch
- ◆ Power management

FEATURES

◆ MOSFET

$V_{DS} = -20V, I_D = -3.4A$

$R_{DS(ON)} < 160m\Omega @ V_{GS} = -1.8V$

$R_{DS(ON)} < 120m\Omega @ V_{GS} = -2.5V$

$R_{DS(ON)} < 90m\Omega @ V_{GS} = -4.5V$

◆ SCHOTTKY

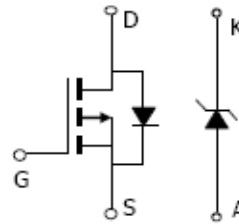
$V_R = 20V, I_F = 1A, V_F < 0.5V @ 0.5A$

- ◆ High Power and current handling capability
- ◆ Surface Mount package

PIN CONFIGURATION



SYMBOL



ORDERING INFORMATION

Part Number	Package
ASM5853F/TR-LF	DFN-8L 3x2mm

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Mosfet	Schottky	Units
Drain-Source Voltage	V_{DS}	-20		V
Gate-Source Voltage	V_{GS}	± 8		V
Drain Current-continuous@Current-pulsed(Notes)	I_D	-3.4		A
	I_{DM}	-15		A
Schottky reverse voltage	V_R		20	V
Continuous Forward Current	I_F		1.9	A
Pulsed Forward Current	I_{FM}		7	A
Maximum Power Dissipation	P_D	1.7	0.96	W
Operating junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^{\circ}C$

Notes: Pulse width limited by maximum junction temperature